

30V N-Channel Enhancement Mode MOSFET

Description

The PECN3402MR uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and high density cell Design for ultra low on-resistance. This device is suitable for use as a load switch or in PWM applications.

General Features

- ◆ $V_{DS} = 30V$, $I_D = 4A$
 $R_{DS(ON)}(Typ.) = 37.5m\Omega$ @ $V_{GS} = 10V$
 $R_{DS(ON)}(Typ.) = 40m\Omega$ @ $V_{GS} = 4.5V$
 $R_{DS(ON)}(Typ.) = 48m\Omega$ @ $V_{GS} = 2.5V$
- ◆ High power and current handling capability
- ◆ Lead free product is acquired
- ◆ Surface mount package

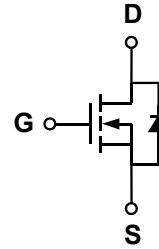
Application

- ◆ PWM applications
- ◆ Load switch

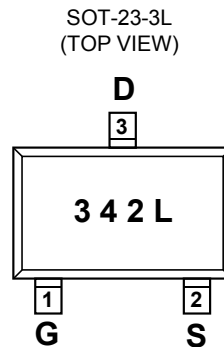
Package

- ◆ SOT-23-3L

Schematic diagram



Marking and pin assignment



342—PECN3402MR
L—Package Information



Ordering Information

| Part Number | Storage Temperature | Package | Devices Per Reel |
|------------------|---------------------|-----------|------------------|
| PECN3402M R-G | -55°C to +150°C | SOT-23-3L | 3000 |

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

| parameter | symbol | limit | unit | |
|--------------------------------------|----------|--------------------|------|---|
| Drain-source voltage | V_{DS} | 30 | V | |
| Gate-source voltage | V_{GS} | ± 12 | V | |
| Continuous Drain Current | I_D | $T_A = 25^\circ C$ | 4 | A |
| | | $T_A = 70^\circ C$ | 3.2 | A |
| Pulsed Drain Current | I_{DM} | 16 | A | |
| Maximum power dissipation | P_D | $T_A = 25^\circ C$ | 1.4 | W |
| | | $T_A = 70^\circ C$ | 0.9 | |
| Operating junction Temperature range | T_j | -55—150 | °C | |

Electrical Characteristics (TA=25°C unless otherwise noted)

| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|---|--------------|---|-----|------|-----------|------------|
| OFF Characteristics | | | | | | |
| Drain-source breakdown voltage | BV_{DSS} | $V_{GS}=0V, I_D=250\mu A$ | 30 | - | - | V |
| Zero gate voltage drain current | I_{DSS} | $V_{DS}=30V, V_{GS}=0V$ | - | - | 1 | μA |
| Gate-body leakage | I_{GSS} | $V_{DS}=0V, V_{GS}=\pm 12V$ | - | - | ± 100 | nA |
| ON Characteristics | | | | | | |
| Gate threshold voltage | $V_{GS(th)}$ | $V_{DS}=V_{GS}, I_D=250\mu A$ | 0.5 | 0.75 | 1.5 | V |
| Drain-source on-state resistance | $R_{DS(ON)}$ | $V_{GS}=10V, I_D=4A$ | - | 37.5 | 45.0 | m Ω |
| | | $V_{GS}=4.5V, I_D=3A$ | | 40.0 | 55.0 | |
| | | $V_{GS}=2.5V, I_D=2A$ | | 48.0 | 65.0 | |
| Forward transconductance | g_{fs} | $V_{GS}=5V, I_D=3.6A$ | - | 14 | - | S |
| Dynamic Characteristics | | | | | | |
| IPECNut capacitance | C_{ISS} | $V_{DS}=15V, V_{GS}=0V$ $f=1.0MHz$ | - | 235 | - | pF |
| Output capacitance | C_{OSS} | | - | 35 | - | |
| Reverse transfer capacitance | C_{RSS} | | - | 18 | - | |
| Switching Characteristics | | | | | | |
| Turn-on delay time | $t_{D(ON)}$ | $V_{DS}=15V$ $V_{GS}=10V$ $R_L=2.6\text{ ohm}$ $R_{GEN}=3\text{ohm}$ | - | 3.5 | - | ns |
| Rise time | t_r | | - | 1.5 | - | |
| Turn-off delay time | $t_{D(OFF)}$ | | - | 17.5 | - | |
| Fall time | t_f | | - | 2.5 | - | |
| Total gate charge | Q_g | $V_{DS}=15V, I_D=4A$ $V_{GS}=10V$ | - | 10 | - | nC |
| Gate-source charge | Q_{gs} | | - | 0.95 | - | |
| Gate-drain charge | Q_{gd} | | - | 1.6 | - | |
| DRAIN-SOURCE DIODE CHARACTERISTICS | | | | | | |
| Diode forward voltage | V_{SD} | $V_{GS}=0V, I_s=1A$ | - | 0.82 | 1.16 | V |

Thermal Characteristics

| Parameter | Symbol | Typ | Max | Unit |
|--|--------------|-----------------|-----|---------------|
| Maximum Junction-to-Ambient ^A | $\leq 10s$ | 65 | 90 | $^{\circ}C/W$ |
| Maximum Junction-to-Ambient ^A | Steady-State | | | |
| Maximum Junction-to-Lead ^B | Steady-State | $R_{\theta JC}$ | 63 | |

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^{\circ}C$. The value in any given application depends on the user's specific board design. The current rating is based on the $t \leq 10s$ thermal resistance rating.

B: The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

Typical Performance Characteristics

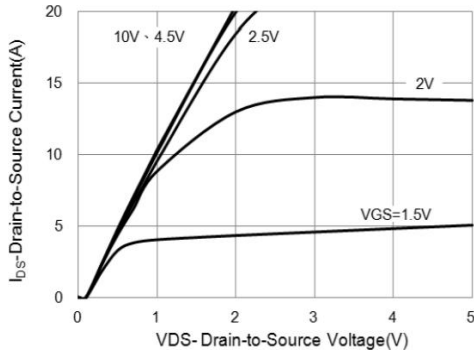


Fig 1: On-Region Characteristics

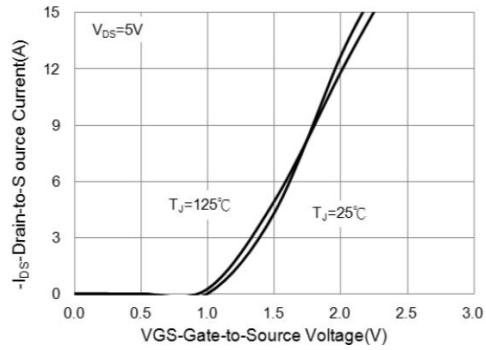


Figure 2: Transfer Characteristics

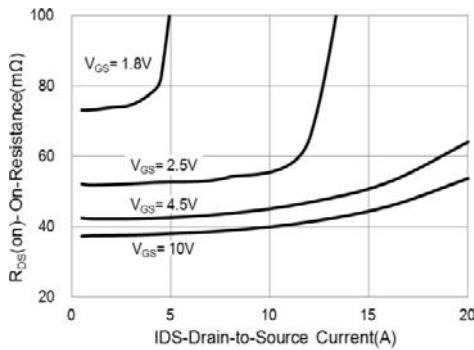


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

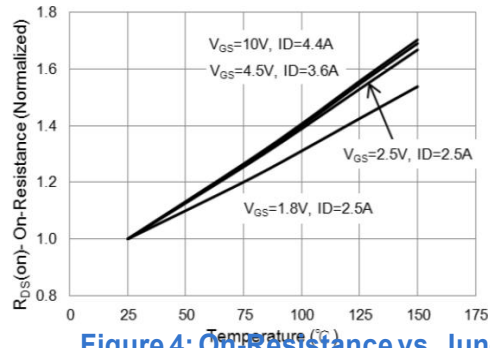


Figure 4: On-Resistance vs. Junction Temperature

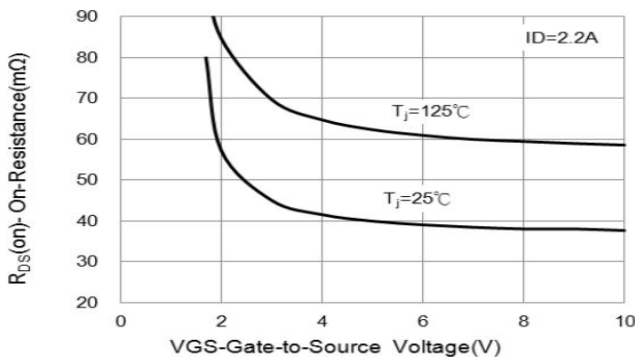


Figure 5: On-Resistance vs. Gate-Source Voltage

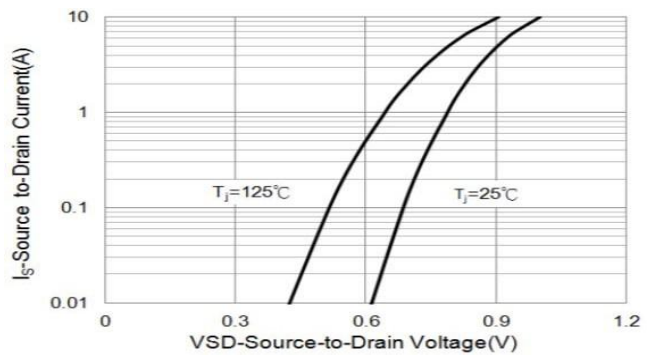


Figure 6: Body-Diode Characteristics

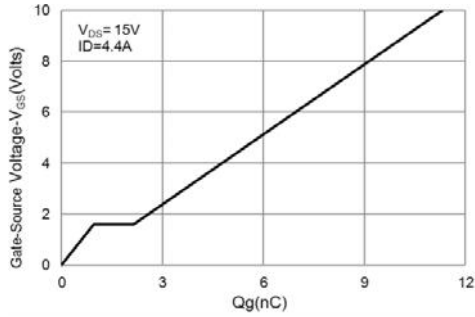


Figure 7: Gate-Charge Characteristics

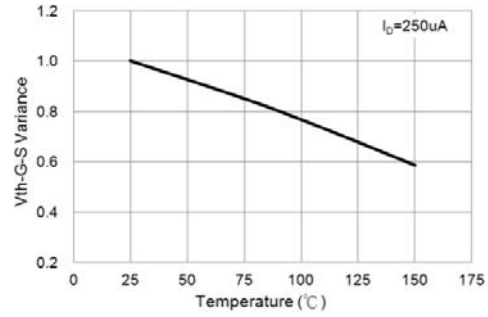
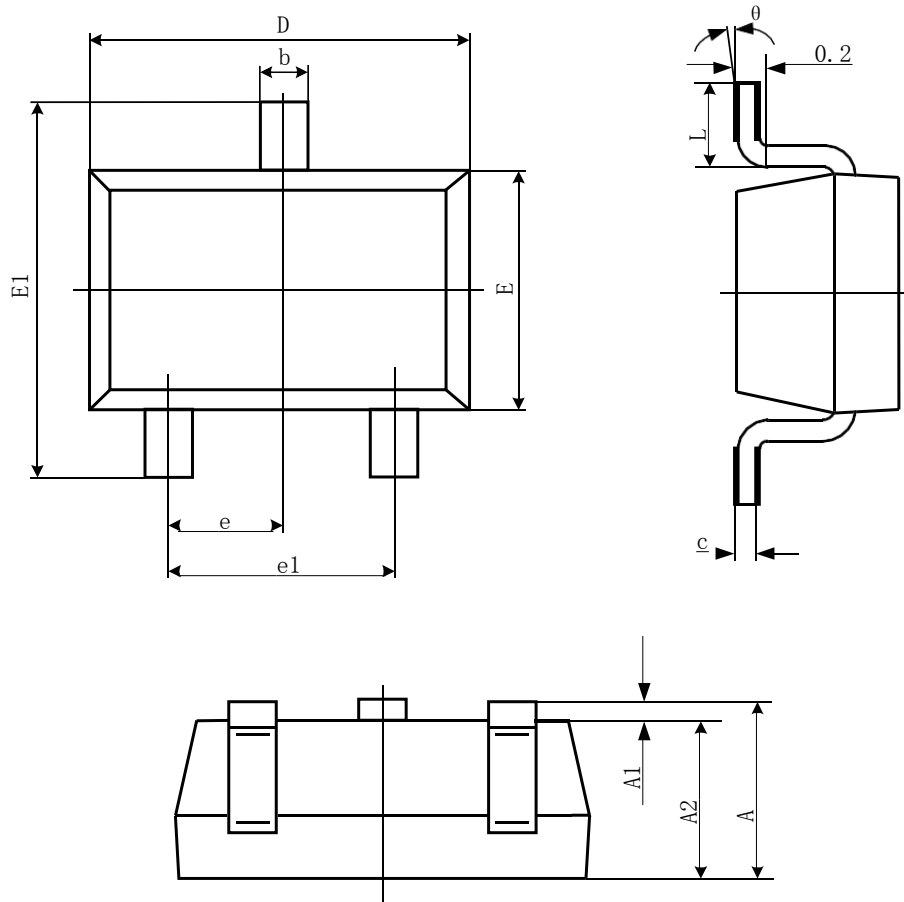


Figure 8: Threshold Voltage Variation with Temperature.

Package Information

- SOT-23-3L



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|--------|---------------------------|-------|----------------------|-------|
| | Min | Max | Min | Max |
| A | 1.050 | 1.250 | 0.041 | 0.049 |
| A1 | 0.000 | 0.100 | 0.000 | 0.004 |
| A2 | 1.050 | 1.150 | 0.041 | 0.045 |
| b | 0.300 | 0.500 | 0.012 | 0.020 |
| c | 0.100 | 0.200 | 0.004 | 0.008 |
| D | 2.820 | 3.020 | 0.111 | 0.119 |
| E | 1.500 | 1.700 | 0.059 | 0.067 |
| E1 | 2.650 | 2.950 | 0.104 | 0.116 |
| e | 0.950(BSC) | | 0.037(BSC) | |
| e1 | 1.800 | 2.000 | 0.071 | 0.079 |
| L | 0.300 | 0.600 | 0.012 | 0.024 |
| θ | 0° | 8° | 0° | 8° |